LECTURE NO 22

Electrostatics

POISSON'S AND LAPLACE'S EQUATIONS

Poisson's and Laplace's equations are easily derived from Gauss's law (for a linear material medium)

$$\nabla \cdot \mathbf{D} = \nabla \cdot \varepsilon \mathbf{E} = \rho_{\nu} \tag{6.1}$$

and

$$\mathbf{E} = -\nabla V \tag{6.2}$$

Substituting eq. (6.2) into eq. (6.1) gives

$$\nabla \cdot (-\varepsilon \nabla V) = \rho_{\nu} \tag{6.3}$$

for an inhomogeneous medium. For a homogeneous medium, eq. (6.3) becomes

$$\nabla^2 V = -\frac{\rho_v}{\varepsilon} \tag{6.4}$$

This is known as *Poisson's equation*. A special case of this equation occurs when $\rho_v = 0$ (i.e., for a charge-free region). Equation (6.4) then becomes

$$\nabla^2 V = 0 \tag{6.5}$$

$$\frac{\partial^2 V}{\partial x^2} + \frac{\partial^2 V}{\partial y^2} + \frac{\partial^2 V}{\partial z^2} = 0$$
 (6.6)

$$\frac{1}{\rho} \frac{\partial}{\partial \rho} \left(\rho \frac{\partial V}{\partial \rho} \right) + \frac{1}{\rho^2} \frac{\partial^2 V}{\partial \phi^2} + \frac{\partial^2 V}{\partial z^2} = 0$$
 (6.7)

$$\frac{1}{r^2} \frac{\partial}{\partial r} \left(r^2 \frac{\partial V}{\partial r} \right) + \frac{1}{r^2 \sin \theta} \frac{\partial}{\partial \theta} \left(\sin \theta \frac{\partial V}{\partial \theta} \right) + \frac{1}{r^2 \sin^2 \theta} \frac{\partial^2 V}{\partial \phi^2} = 0$$
 (6.8)

RESISTANCE AND CAPACITANCE

In Section 5.4 the concept of resistance was covered and we derived eq. (5.16) for finding the resistance of a conductor of uniform cross section. If the cross section of the conductor is not uniform, eq. (5.16) becomes invalid and the resistance is obtained from eq. (5.17):

$$R = \frac{V}{I} = \frac{\int \mathbf{E} \cdot d\mathbf{I}}{\oint \sigma \mathbf{E} \cdot d\mathbf{S}}$$
 (6.16)

A. Parallel-Plate Capacitor

Consider the parallel-plate capacitor of Figure 6.13(a). Suppose that each of the plates has an area S and they are separated by a distance d. We assume that plates 1 and 2, respectively, carry charges +Q and -Q uniformly distributed on them so that

$$\rho_S = \frac{Q}{S} \tag{6.19}$$

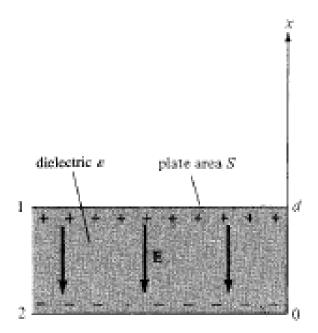


Figure 6.13 (a) Parallel-plate capacitor, (b) fringing effect due to a parallel-plate capacitor.

An ideal parallel-plate capacitor is one in which the plate separation d is very small compared with the dimensions of the plate. Assuming such an ideal case, the fringing field at the edge of the plates, as illustrated in Figure 6.13(b), can be ignored so that the field between them is considered uniform. If the space between the plates is filled with a homogeneous dielectric with permittivity ε and we ignore flux fringing at the edges of the plates, from eq. (4.27), $\mathbf{D} = -\rho_S \mathbf{a}_x$ or

$$\mathbf{E} = \frac{\rho_S}{\varepsilon} (-\mathbf{a}_x)$$

$$= -\frac{Q}{\varepsilon S} \mathbf{a}_x$$
(6.20)

Hence

$$V = -\int_{2}^{1} \mathbf{E} \cdot d\mathbf{I} = -\int_{0}^{d} \left[-\frac{Q}{\varepsilon S} \mathbf{a}_{x} \right] \cdot dx \, \mathbf{a}_{x} = \frac{Qd}{\varepsilon S}$$
 (6.21)

and thus for a parallel-plate capacitor

$$C = \frac{Q}{V} = \frac{\dot{\epsilon S}}{d}$$
 (6.22)

This formula offers a means of measuring the dielectric constant ε_r of a given dielectric. By measuring the capacitance C of a parallel-plate capacitor with the space between the plates filled with the dielectric and the capacitance C_o with air between the plates, we find ε_r from

$$\varepsilon_r = \frac{C}{C_p}$$
(6.23)

Using eq. (4.96), it can be shown that the energy stored in a capacitor is given by

$$W_E = \frac{1}{2} CV^2 = \frac{1}{2} QV = \frac{Q^2}{2C}$$
 (6.24)

To verify this for a parallel-plate capacitor, we substitute eq. (6.20) into eq. (4.96) and obtain

$$W_E = \frac{1}{2} \int_{v} \varepsilon \frac{Q^2}{\varepsilon^2 S^2} dv = \frac{\varepsilon Q^2 S d}{2\varepsilon^2 S^2}$$
$$= \frac{Q^2}{2} \left(\frac{d}{\varepsilon S}\right) = \frac{Q^2}{2C} = \frac{1}{2} QV$$

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